

January 2008

# FJPF1943 PNP Epitaxial Silicon Transistor

### **Applications**

- · High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier

### **Features**

- High Current Capability: I<sub>C</sub> = -15A.
- High Power Dissipation : 50watts.
- High Fequency: 30MHz.
- High Voltage : V<sub>CEO</sub>= -230V
- · Wide S.O.A for reliable operation.
- · Excellent Gain Linearity for low THD.
- Complement to FJPF5200
- Full thermal and electrical Spice models are available.
- · Same transistor is also available in:
  - -- TO264 package, 2SA1943/FJL4215 : 150 watts
  - -- TO3P package, 2SA1962/FJA4213: 130 watts
  - -- TO220 package, FJP1943: 80 watts



### 1.base 2.Collector 3.Emitter

### Absolute Maximum Ratings\* Ta = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV <sub>CBO</sub>	Collector-Base Voltage	-230	V	
BV <sub>CEO</sub>	Collector-Emitter Voltage	-230	V	
BV <sub>EBO</sub>	BV <sub>EBO</sub> Emitter-Base Voltage		V	
I <sub>C</sub>	Collector Current	-15	А	
I <sub>B</sub> Base Current		-1.5	А	
P <sub>D</sub> Total Device Dissipation(T <sub>C</sub> =25°C) Derate above 25°C		50 0.4	W W/°C	
T <sub>J</sub> , T <sub>STG</sub> Junction and Storage Temperature		- 50 ~ +150	°C	

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

# $\textbf{Thermal Characteristics*} \quad \textbf{T}_{a} = 25 \, ^{\circ} \textbf{C} \text{ unless otherwise noted}$

Symbol	Parameter	Ratings	Units
$R_{ heta JC}$	Thermal Resistance, Junction to Case	2.5	°C/W

<sup>\*</sup> Device mounted on minimum pad size

### **h**<sub>FE</sub> Classification

Classification	R	0
h <sub>FE1</sub>	55 ~ 110	80 ~ 160

# **Electrical Characteristics\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =-5mA, I <sub>E</sub> =0	-230			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =-10mA, R <sub>BE</sub> =∞	-230			٧
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =-5mA, I <sub>C</sub> =0	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =-230V, I <sub>E</sub> =0			-5.0	μА
I <sub>EBO</sub> Emitter Cut-off Current		V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-5.0	μА
h <sub>FE1</sub> DC Current Gain		V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A	55		160	
h <sub>FE2</sub> DC Current Gain		V <sub>CE</sub> =-5V, I <sub>C</sub> =-7A	35	60		
V <sub>CE</sub> (sat) Collector-Emitter Saturation Voltage		I <sub>C</sub> =-8A, I <sub>B</sub> =-0.8A		-0.4	-3.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =-5V, I <sub>C</sub> =-7A		-1.0	-1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A		30		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =-10V, f=1MHz		360		pF

<sup>\*</sup> Pulse Test: Pulse Widt=20μs, Duty Cycle≤2%

# **Ordering Information**

Part Number	Marking	Package	Packing Method	Remarks
FJPF1943RTU	J1943R	TO-220F	TUBE	hFE1 R grade
FJPF1943OTU	J1943O	TO-220F	TUBE	hFE1 O grade

# **Typical Characteristics**

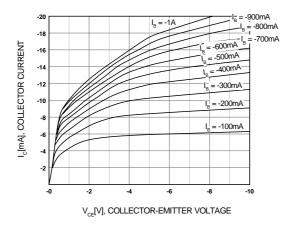


Figure 1. Static Characteristic

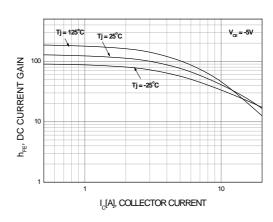


Figure 2. DC current Gain

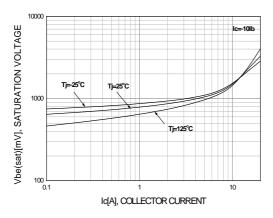


Figure 3. Base-Emitter Saturation Voltage

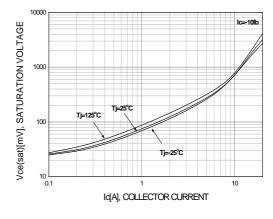


Figure 4. Collector-Emitter Saturation Voltage

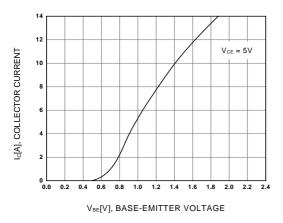


Figure 5. Base-Emitter On Voltage

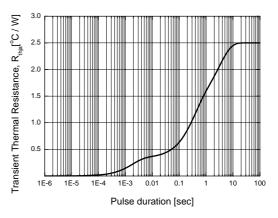


Figure 6. Thermal Resistance

# **Typical Characteristics**

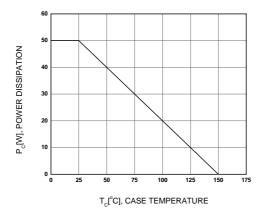


Figure 7. Power Derating





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